


 Cite this: *RSC Adv.*, 2017, 7, 10557

## Correction: The polarization-dependent anisotropic Raman response of few-layer and bulk $\text{WTe}_2$ under different excitation wavelengths

 Qingjun Song,<sup>ab</sup> Haifeng Wang,<sup>cd</sup> Xiaolong Xu,<sup>ab</sup> Xingchen Pan,<sup>cd</sup> Yilun Wang,<sup>ab</sup> Fengqi Song,<sup>cd</sup> Xiangang Wan<sup>\*cd</sup> and Lun Dai<sup>\*ab</sup>

DOI: 10.1039/c7ra90007d

[www.rsc.org/advances](http://www.rsc.org/advances)

 Correction for 'The polarization-dependent anisotropic Raman response of few-layer and bulk  $\text{WTe}_2$  under different excitation wavelengths' by Qingjun Song *et al.*, *RSC Adv.*, 2016, 6, 103830–103837.

In part (d) of Fig. 4 of the original manuscript, and in the description of part (d) in the Fig. 4 caption, the wrong labels were given for the modes. The labels “ $B_g$ ” and “ $A_u$ ” should be “ $B_u$ ” and “ $A_g$ ”, respectively. The corrected Fig. 4 and its caption are shown below:

Additionally, in the Results and Discussion section, in the text below Fig. 4, two sentences should be revised as follows:

“For  $E_{\text{las}} \approx 2.3$  eV, the excited electron will transit from the  $A_g$  valence band to  $A_u$  conductance band, and the corresponding polar plot is shown in Fig. 4(e), where the maximum (minimum) absorption corresponds to the perpendicular (parallel) relation between the incident polarization and  $a$ -axis”.

“To study the influence of electron–photon interaction on the anisotropic Raman scattering, we first assume the electron–phonon interaction ( $H_{e-ph}$ ) in the Raman scattering is not polarization dependent”.

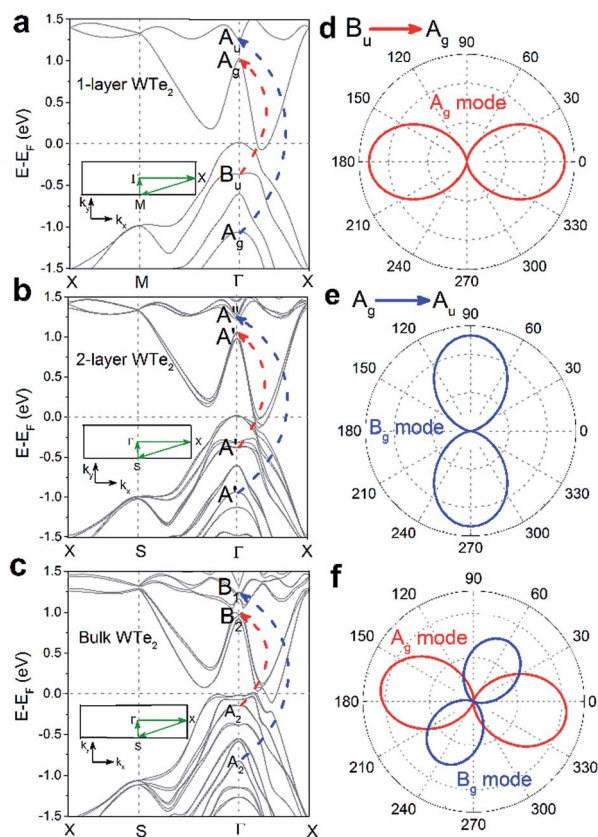
<sup>a</sup>State Key Lab for Mesoscopic Physics, School of Physics, Peking University, Beijing 100871, China. E-mail: [lundai@pku.edu.cn](mailto:lundai@pku.edu.cn)

<sup>b</sup>Collaborative Innovation Center of Quantum Matter, Beijing 100871, China

<sup>c</sup>National Laboratory of Solid State Microstructures, College of Physics, Nanjing University, Nanjing 210093, China. E-mail: [xgwan@nju.edu.cn](mailto:xgwan@nju.edu.cn)

<sup>d</sup>Collaborative Innovation Center of Advanced Microstructures, Nanjing University, Nanjing 210093, China





**Fig. 4** (a–c) The calculated band structures of monolayer, bilayer and bulk WTe<sub>2</sub>, respectively. The representative band symmetries at  $\Gamma$  point are labelled, and the insets are their 2D Brillouin zones. Calculated polarization dependence of the optical transition probability (d) from the  $B_u$  to  $A_g$  ( $E_{\text{ias}} \approx 1.5$  eV) and (e) from the  $A_g$  to  $A_u$  ( $E_{\text{ias}} \approx 2.3$  eV) in monolayer WTe<sub>2</sub>, as indicated in (a).  $0^\circ$  corresponds to the W–W chain ( $a$ -axis) direction, the initial incident polarization and scattered polarization are along the  $a$ -axis ( $\theta_0 = 0^\circ$ ). (f) The representative calculated polarization dependent intensities of  $A_g$  and  $B_g$  modes in monolayer WTe<sub>2</sub> with certain  $\theta_0$  ( $\sim 15^\circ$ ).

The Royal Society of Chemistry apologises for these errors and any consequent inconvenience to authors and readers.

